

Gigatracker Demonstrator Design review

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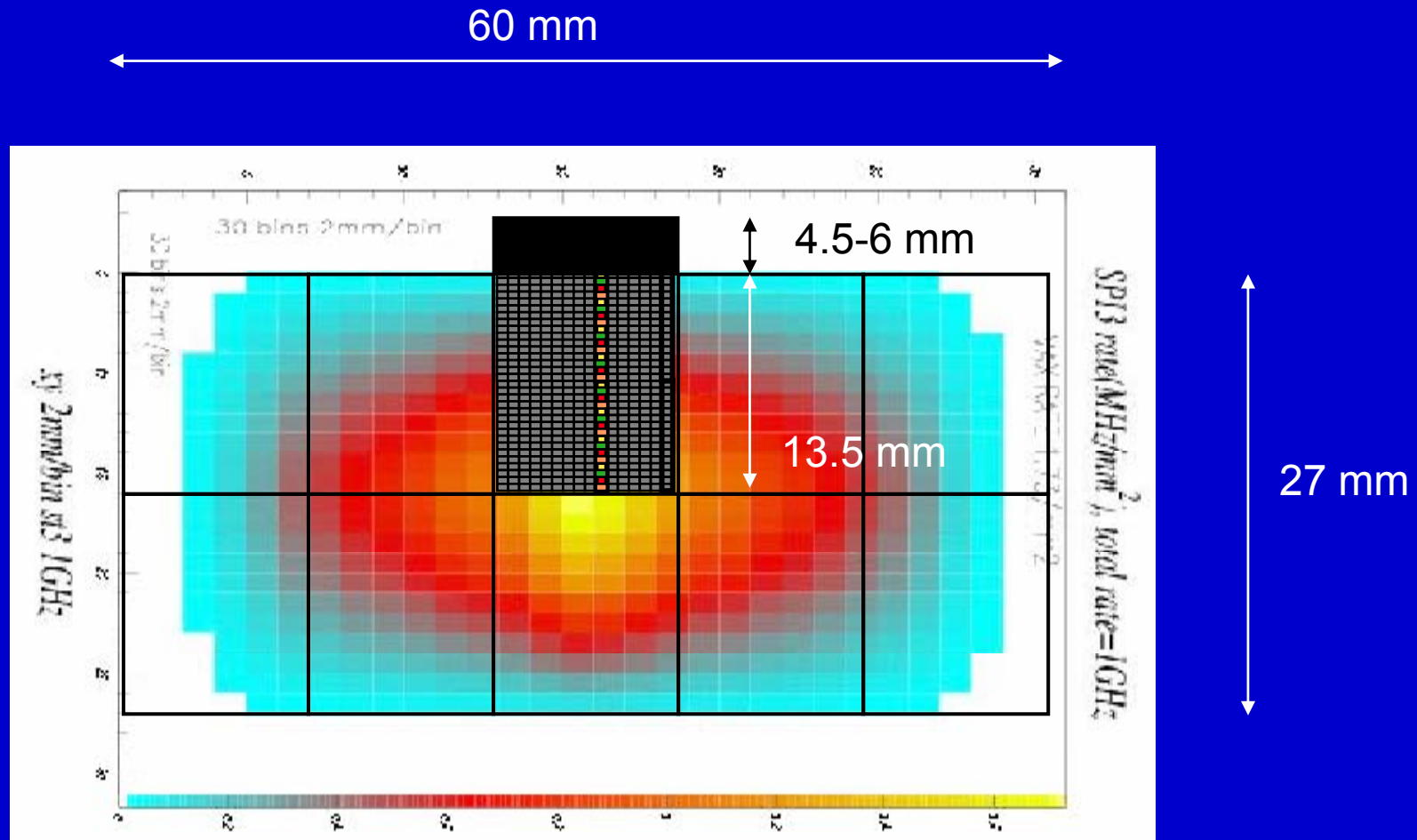
Scope

- **System introduction**
- **Specifications**
- **Design options**

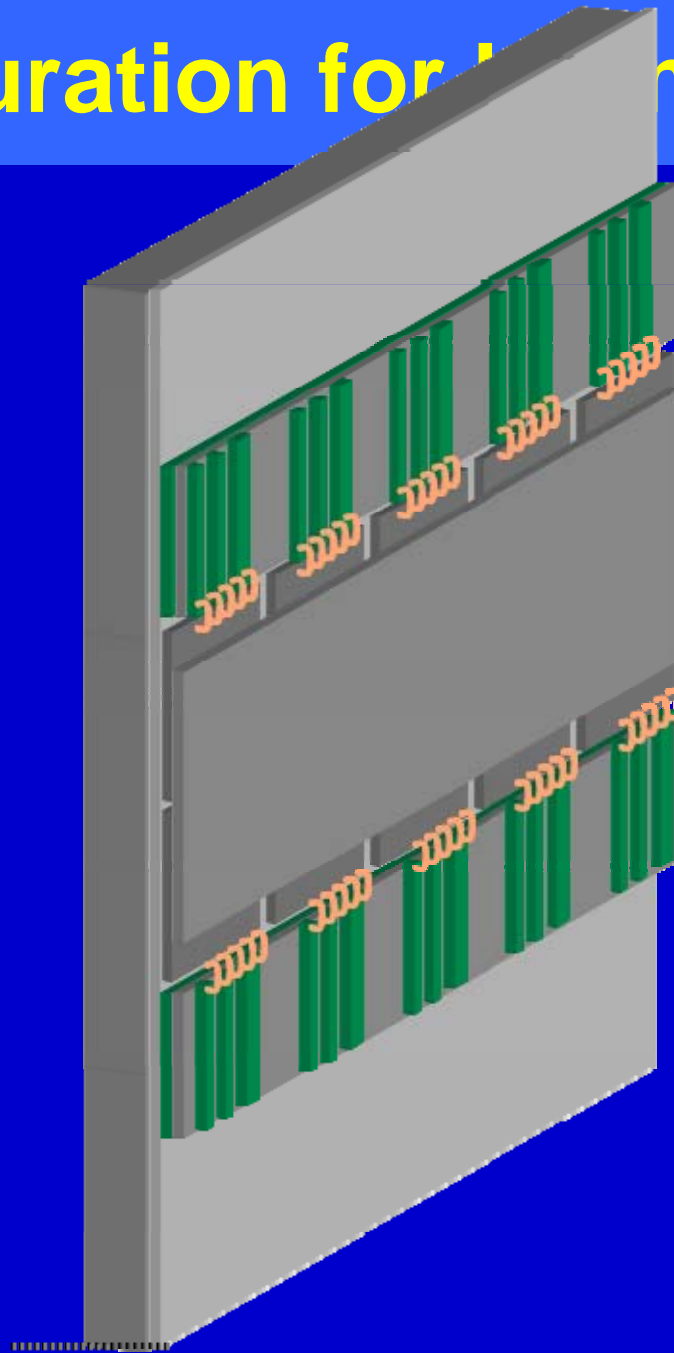
27-60 Beam size & pixel matrix

- Beam geometry size -> 27 x 60 mm
- 3 stations: each 5 x 2 ASICs + 1 sensor
- Active pixel matrix size per chip: 13.5 x 12 mm
- 45 rows x 40 columns = 1800 pixels
- Each pixel 300 μm x 300 μm
- Time stamping: < 200 ps rms in one station

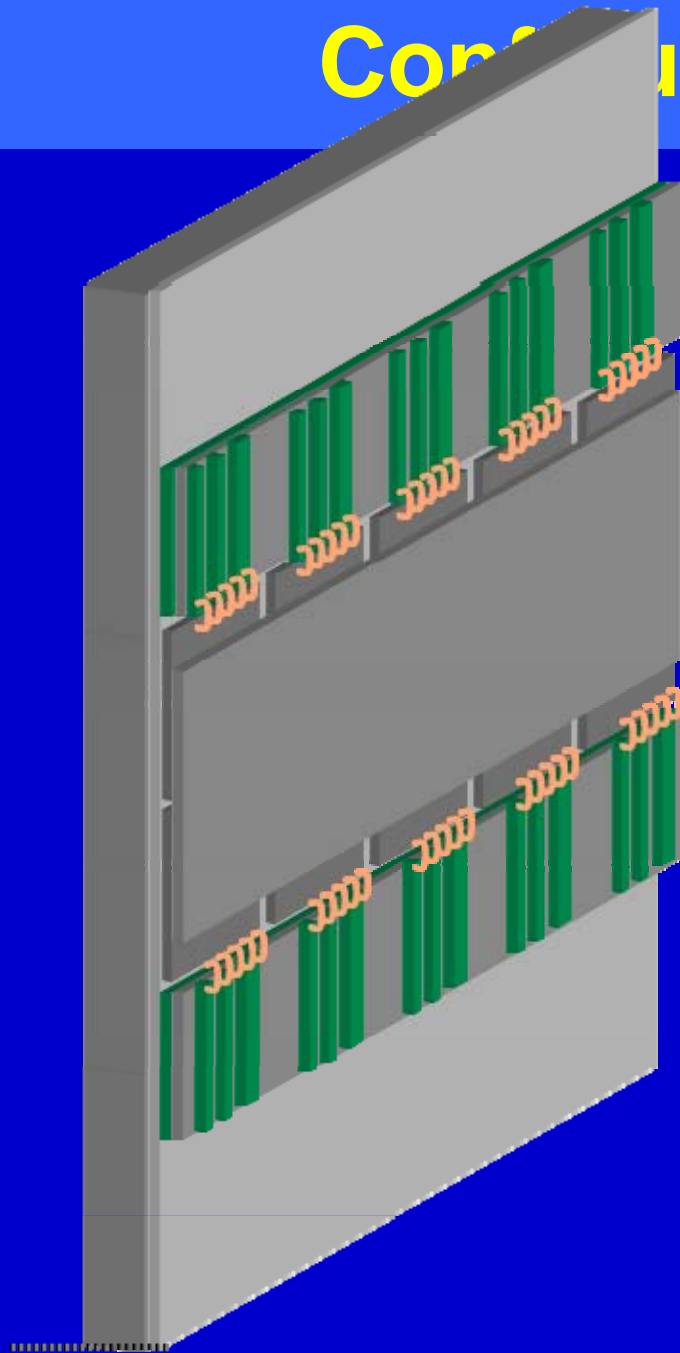
Configuration



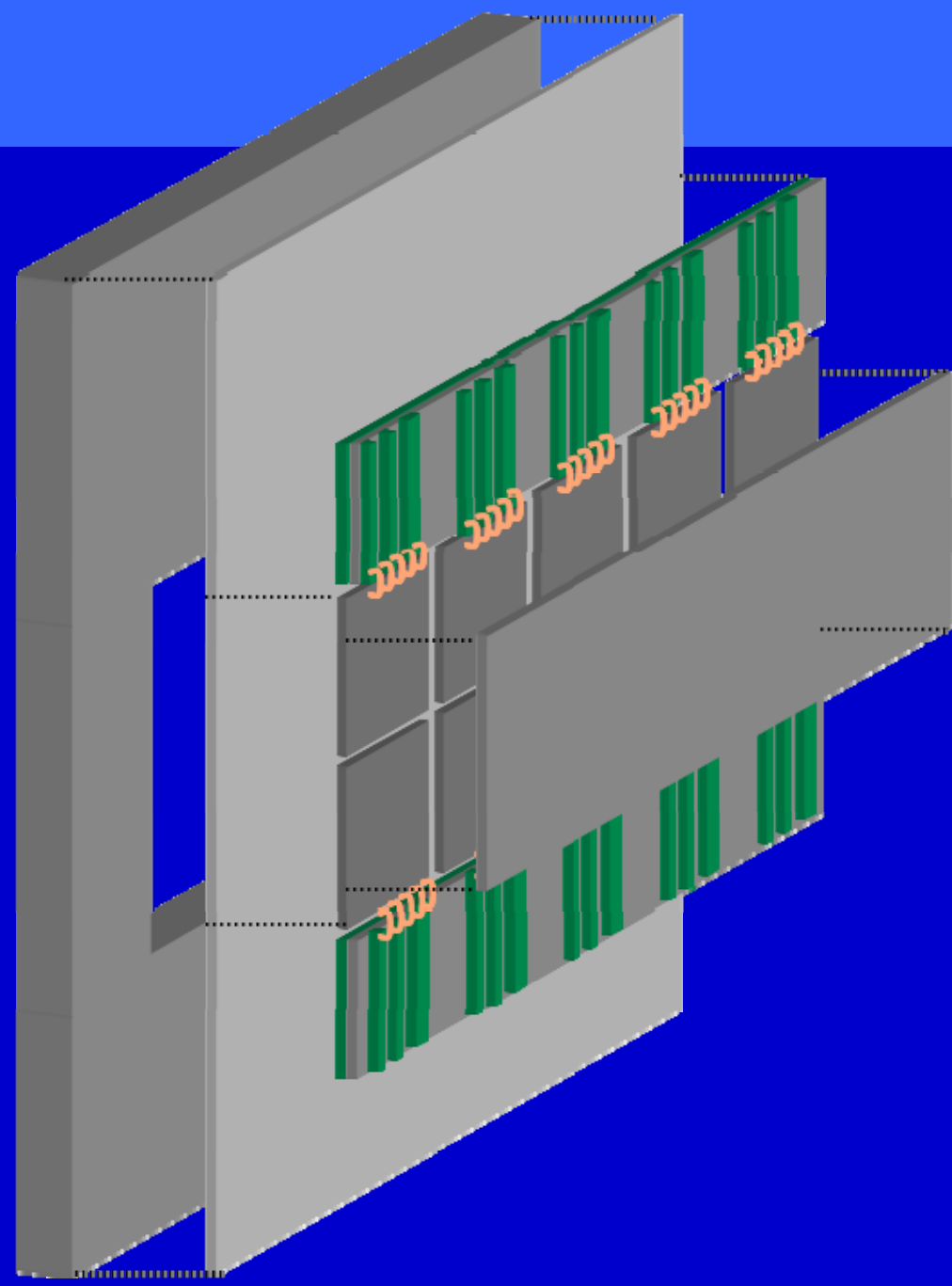
Configuration for Form 27-60



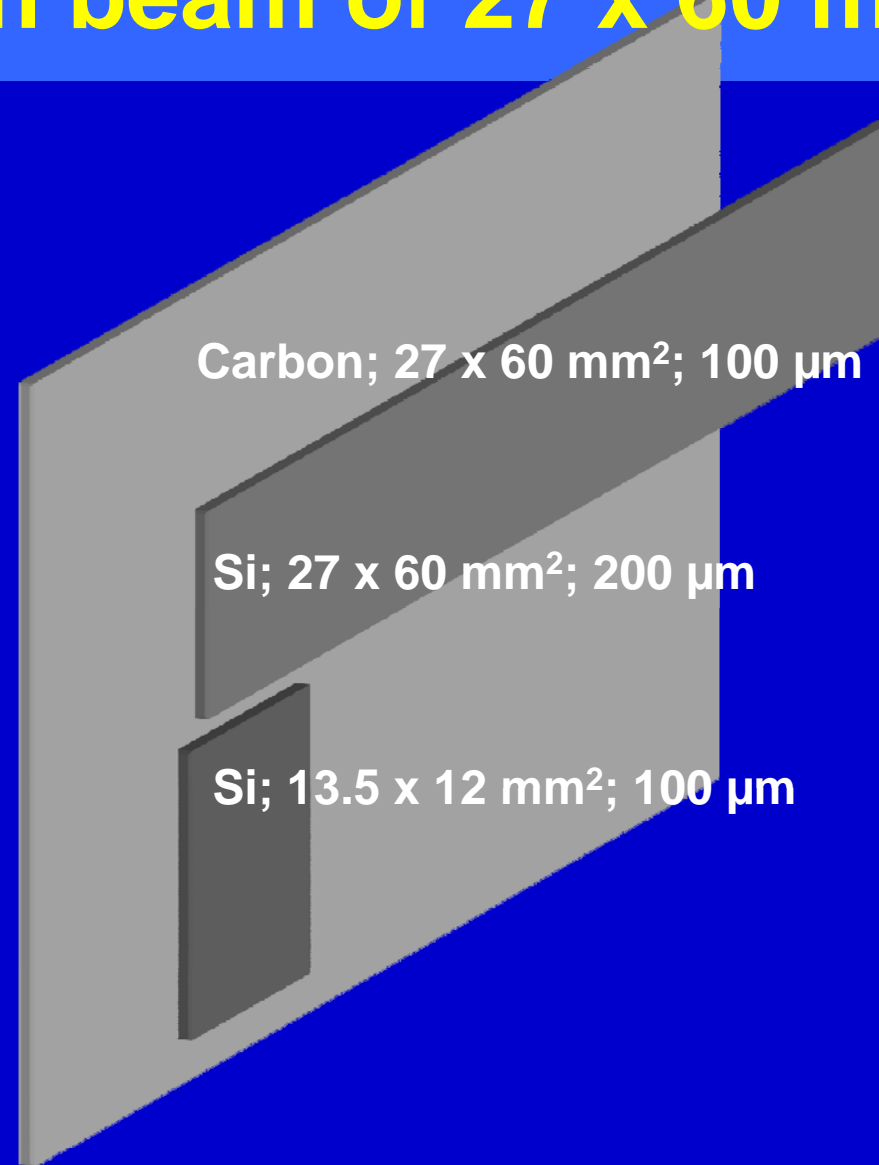
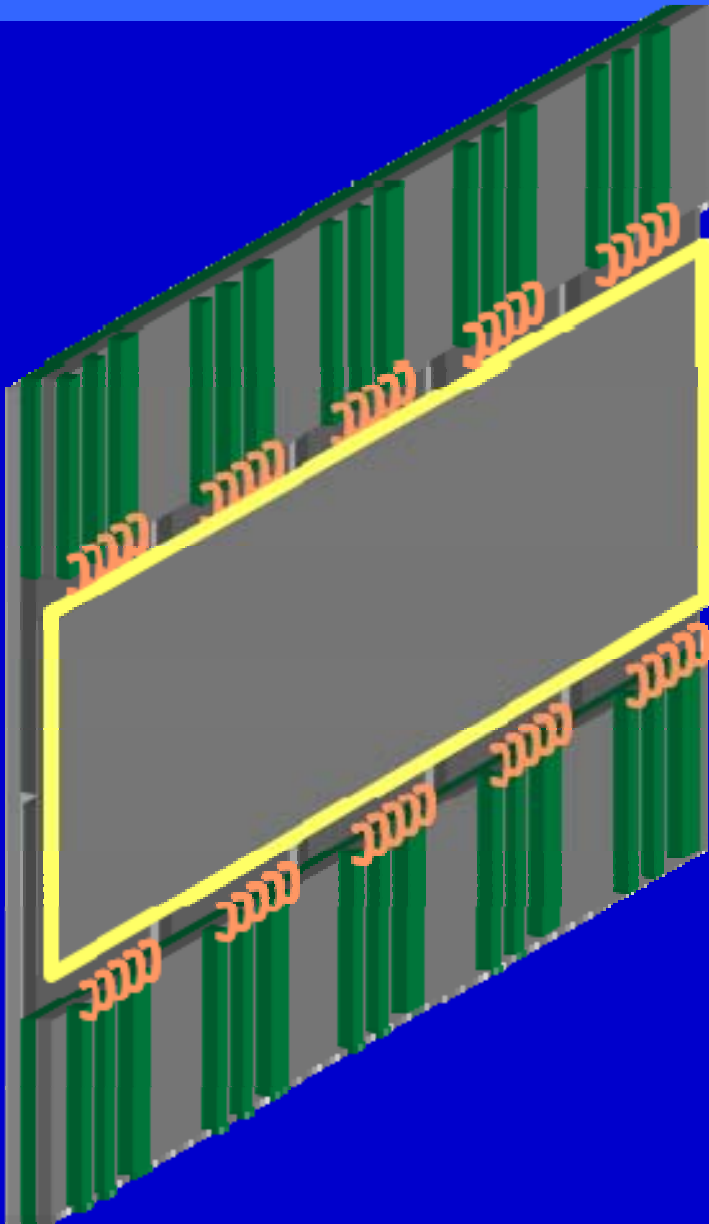
Configuration for beam 27-60



- **Sensor&bonds: 0.24% X_0**
(200 μm Silicon)
- **RO chip: 0.11% X_0**
(100 μm Silicon)
- **Structure: 0.10% X_0**
(100 μm Carbon fiber)
- **Total: 0.45% X_0 uniform**



Components in beam of 27 x 60 mm



Carbon; 27 x 60 mm²; 100 μm

Si; 27 x 60 mm²; 200 μm

Si; 13.5 x 12 mm²; 100 μm

General: System Specifications

Number of stations	3
Number of pixels per station	18000
Active area per station	60 mm x 27 mm = 1620 mm ²
Number of chips per station	2 rows x 5 columns
Number of pixels per chip	1800
Rows and columns on chip	45 x 40
Size of pixels	300 μm x 300 μm
Active area per chip	12 mm x 13.5 mm = 162 mm ²
Time resolution of GTK	150 ps (rms)
Time resolution of one station	< 200 ps (rms)
Chip design time resolution	100 ps (rms)

General: System Specifications

Size of active sensor area	60 mm x 27 mm = 1620 mm ²
Thickness of sensor	200 μm
Type of sensor	p in n
Thickness of read-out chip	100 μm
Dynamic input range	5000 – 60000 electrons
Particle rate per station	800 MHz
Average particle intensity per station	0.5 MHz/mm ²
Design particle rate per chip	130 MHz
Rate of center pixel	140 kHz
Rate of center column	~ 3.3 MHz or 0.82 MHz/mm ²
Average rate per pixel	73 kHz

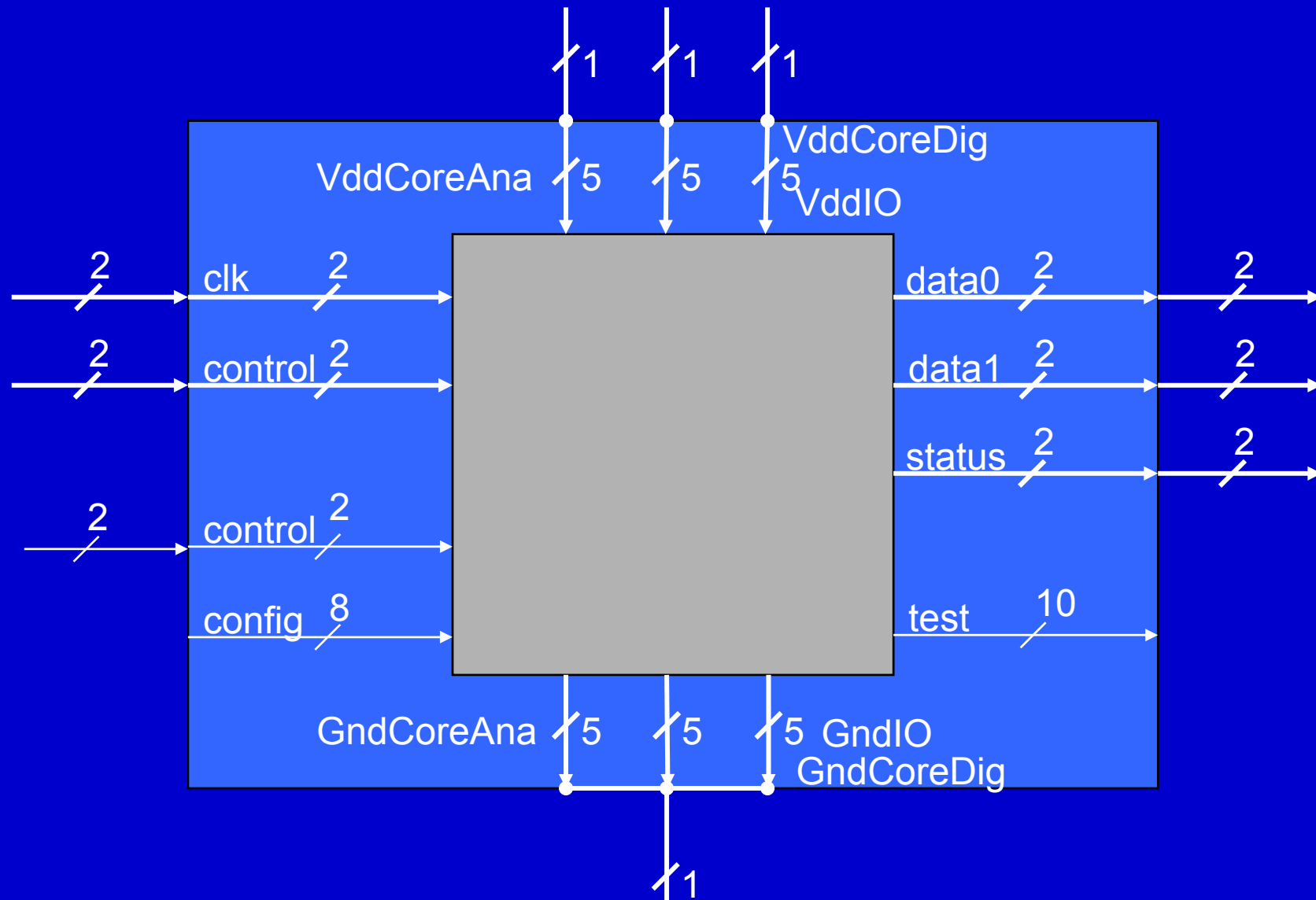
General: System Specifications

Number of trigger levels	1
Latency	> 1 μ s up to 1 ms
Trigger window	\geq 10 ns
Maximum dead time	1 % (2 % in beam center)
Data transfer rate per chip	6 Gbit/s
Total dose in 1 year	$\sim 10^5$ Gy
Neutron flux in 100 days	2×10^{14} 1 MeV neutron equivalent cm^{-2}
Material budget	0.5 % X_0 per station
Power dissipation per station	≤ 2 W/ cm^2 , 32 W
Operating temperature per station	< 0 $^{\circ}\text{C}$

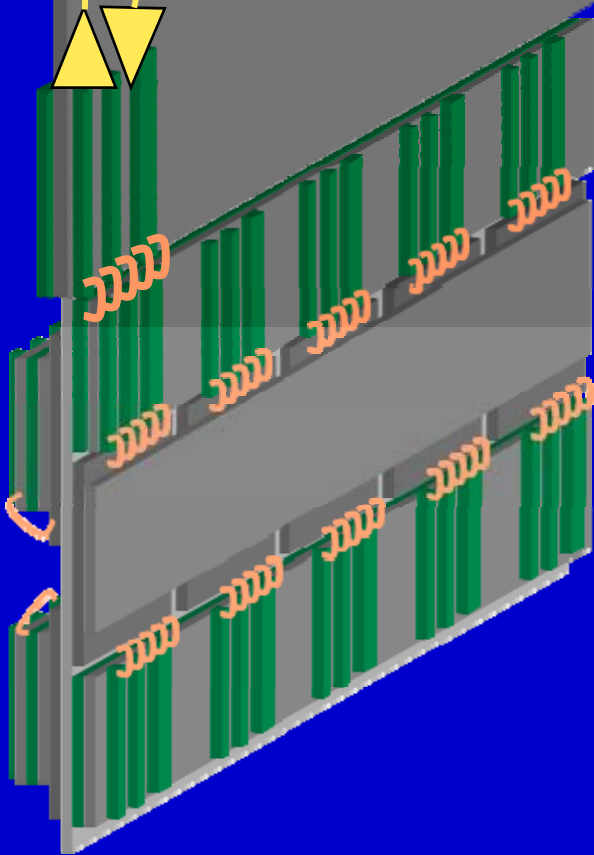
Chip size/data rate

- Rate of center column = chip design rate:
 - 3.3 MHz/column
 - $3.3 \text{ MHz}/(1.35 \text{ cm} * 0.03 \text{ cm})$
 - $\sim 82 \text{ MHz/cm}^2$
- => avg rate 73 kHz/pixel
- => 132 MHz/chip
- => $132 \text{ MHz/chip} * \sim 32 \text{ bit} = \sim 4.2 \text{ Gbit/s}$
- => max rate in beam center 140 kHz/pixel
- Example data word (11 bit address, 5 bit fine time, (5 bit fine time trailing), 11 bit coarse time)

I/O block diagram of chip



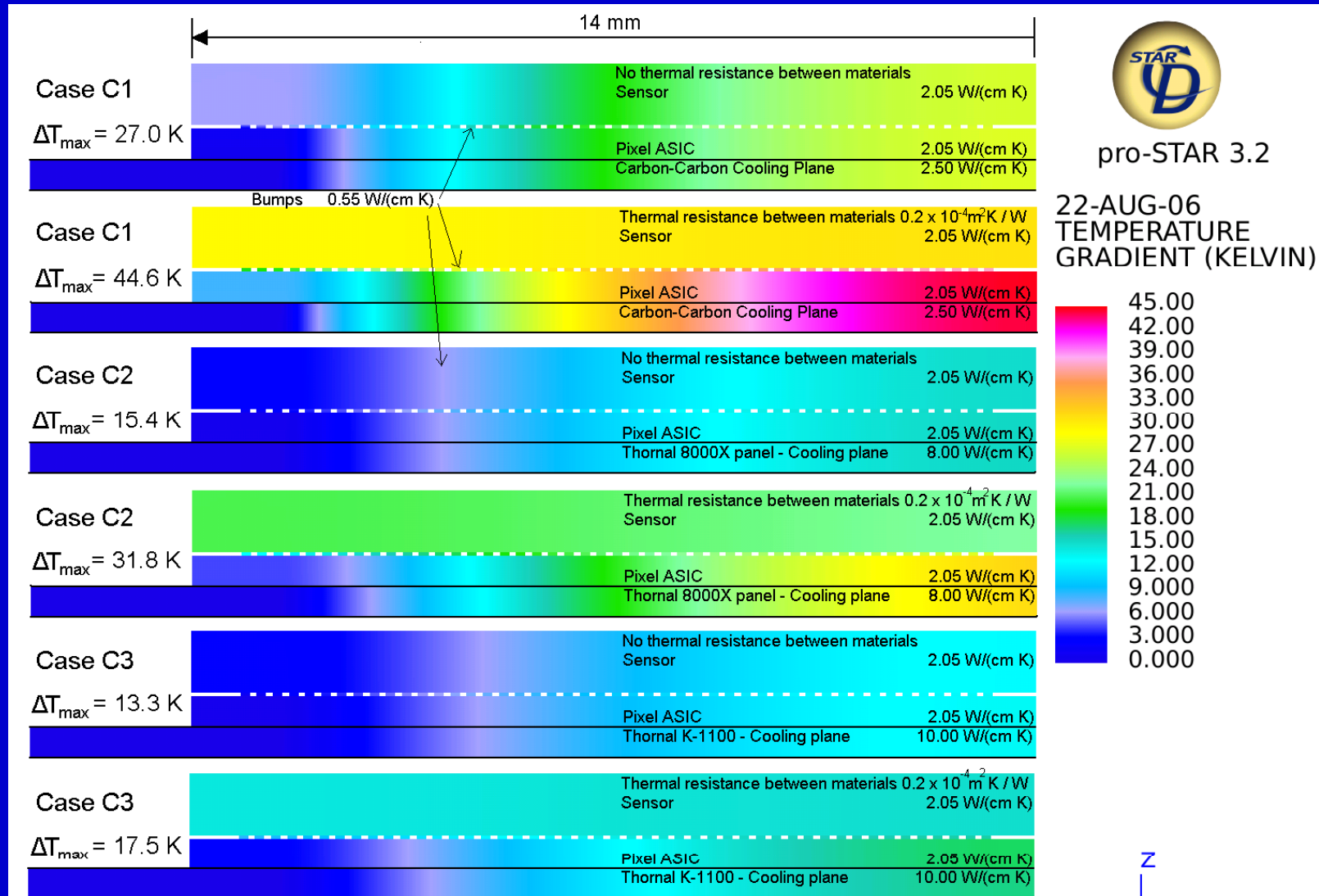
Read out



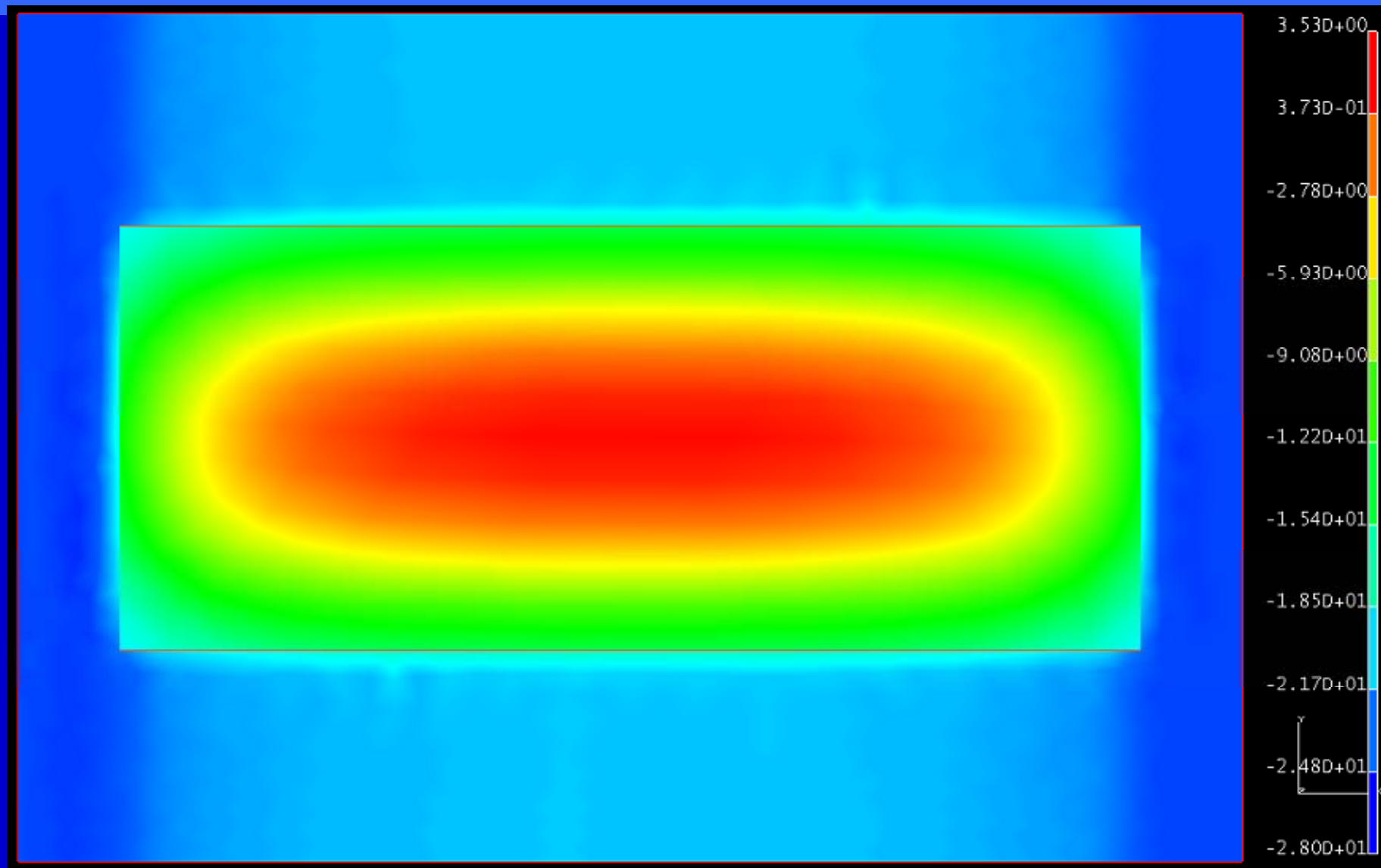
- 3 planes x 2 x 5 chips x (>2 high speed + >1 low speed + 1 clock) optical links = >60 high speed links + >30 low speed links + >30 clock links
- On-detector is trigger-less

Thermal drop: ideal contact between materials (Thomas Kuhn)

<https://edms.cern.ch/document/761753/1>



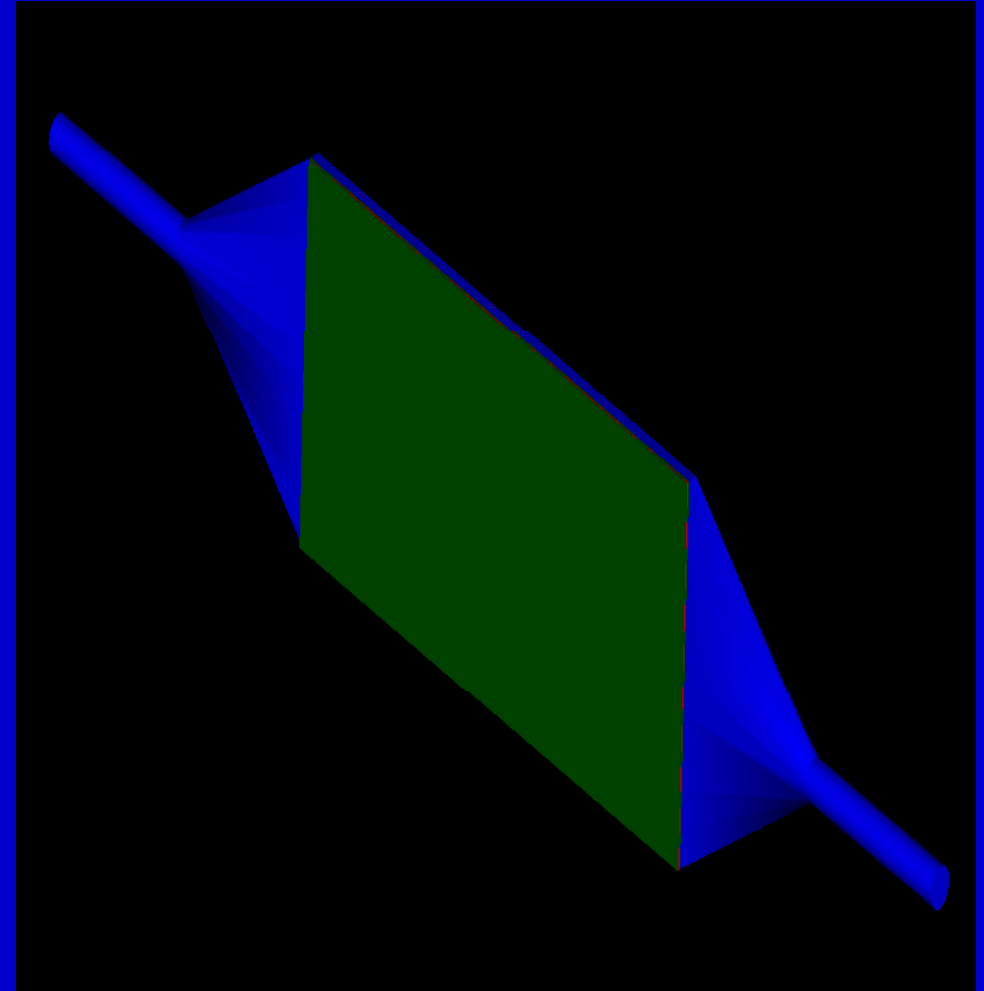
CONFIGURATION 1 – TEMPERATURE DISTRIBUTION



CONFIGURATION 2 – COOLING ANALISYS

COOLING FLUID : NITROGEN		K	°C
Delivery temperature	Ti	100	-173
Wall temperature	Tw	273	0
Mean temperature	$T_m = (T_i + T_w)/2$	186,5	-86,5

NITROGEN PROPERTIES @ Tm and atmospheric pressure		
Specific weight (Kg/m ³)	ρ	1,79
Specific heat (J/KgK)	Cp	1041
Thermal conductivity (W/mK)	λ	0,024
Kinematic viscosity (m ² /s)	ν	1,34E-05

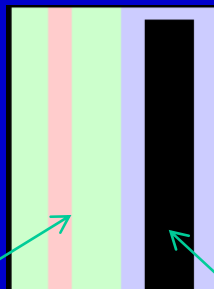


GENERATED POWER (W)

$$Q = q \times A = (2E+04) \times (27E-03 \times 60E-03) = 32,4$$

COOLING CIRCUIT SURFACE (m²)

$$S = 27E-03 \times 60E-03 = 1,62E-03$$



DETECTO
R

COOLING BOX

Vittore Carassiti - INFN FE

MAX dT (°C) (sensors side)

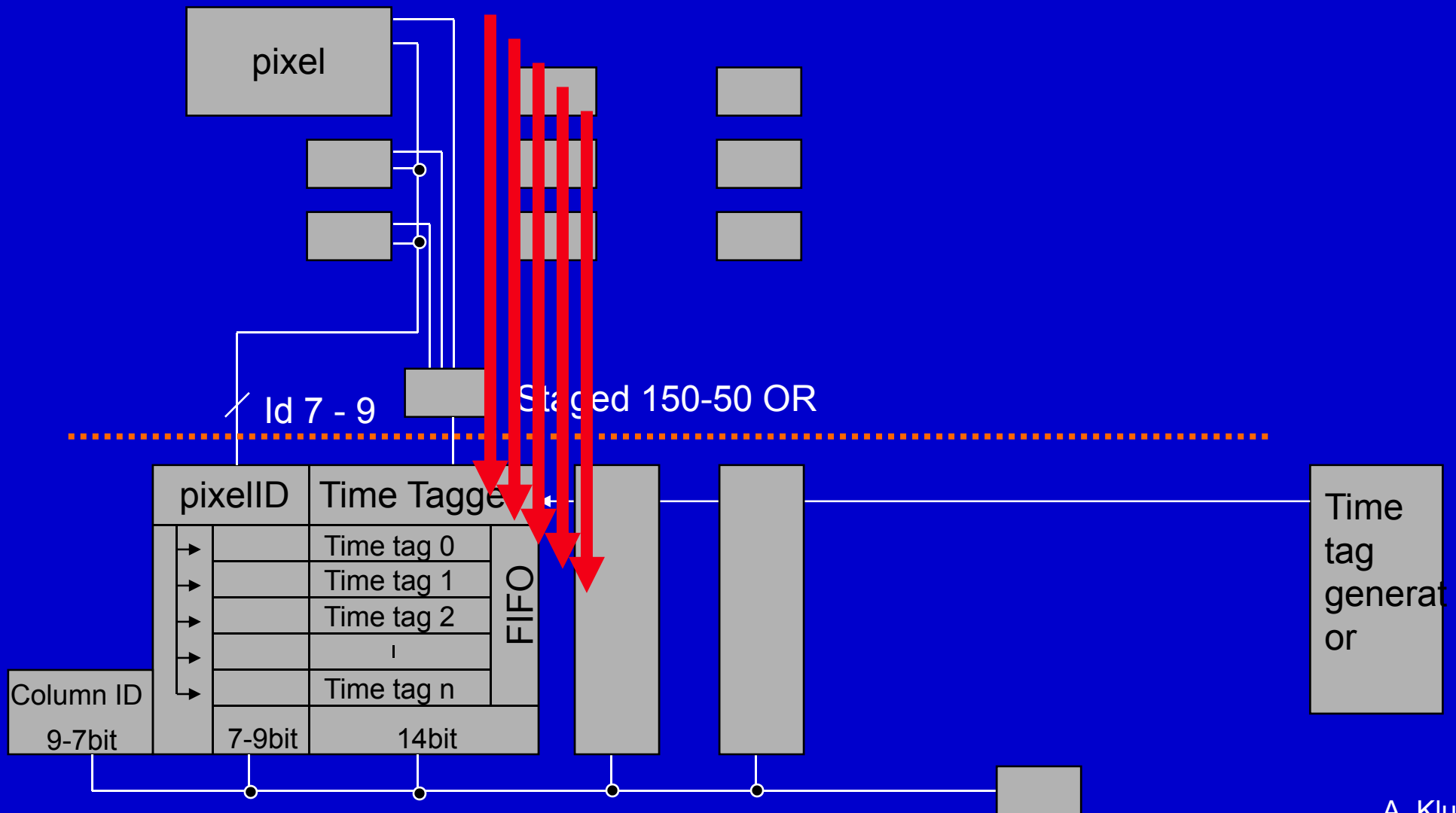
conf 1 23,5

conf 20,2

General architecture

- **Small signal, time walk \leftrightarrow timing precision**
Low noise \leftrightarrow digital electronics, high data rate
- **Pixel segmentation**
Efficiency \leftrightarrow dead time

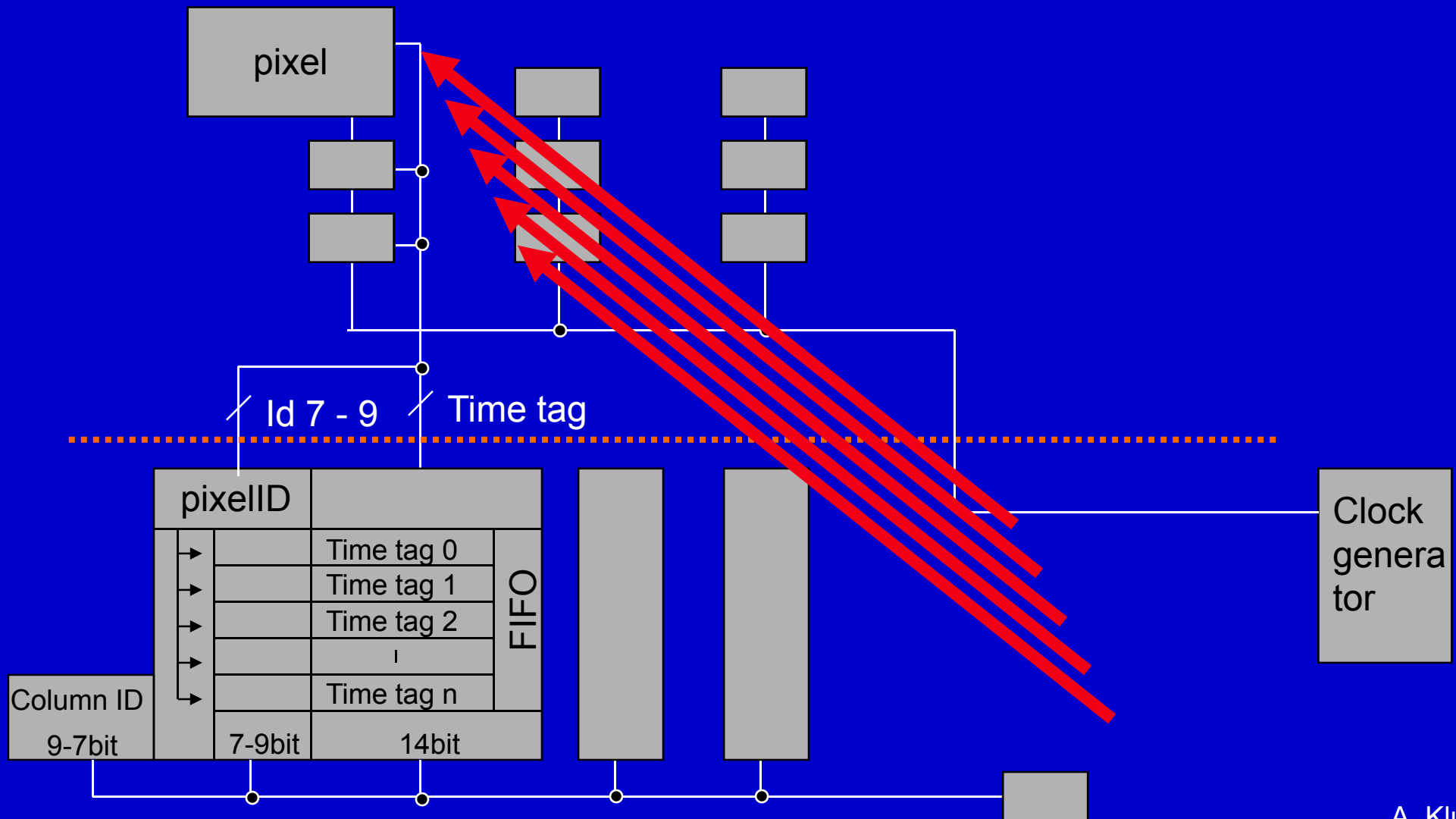
Precise pixel signal to TDC



Precise pixel signal to TDC

- Many low jitter signals are routed over the chip and over pixel cells to central high frequency time tag TDC
- Long low jitter signal lines
- Digital electronics in periphery
Noise separation, SEU

TDC in pixel cell

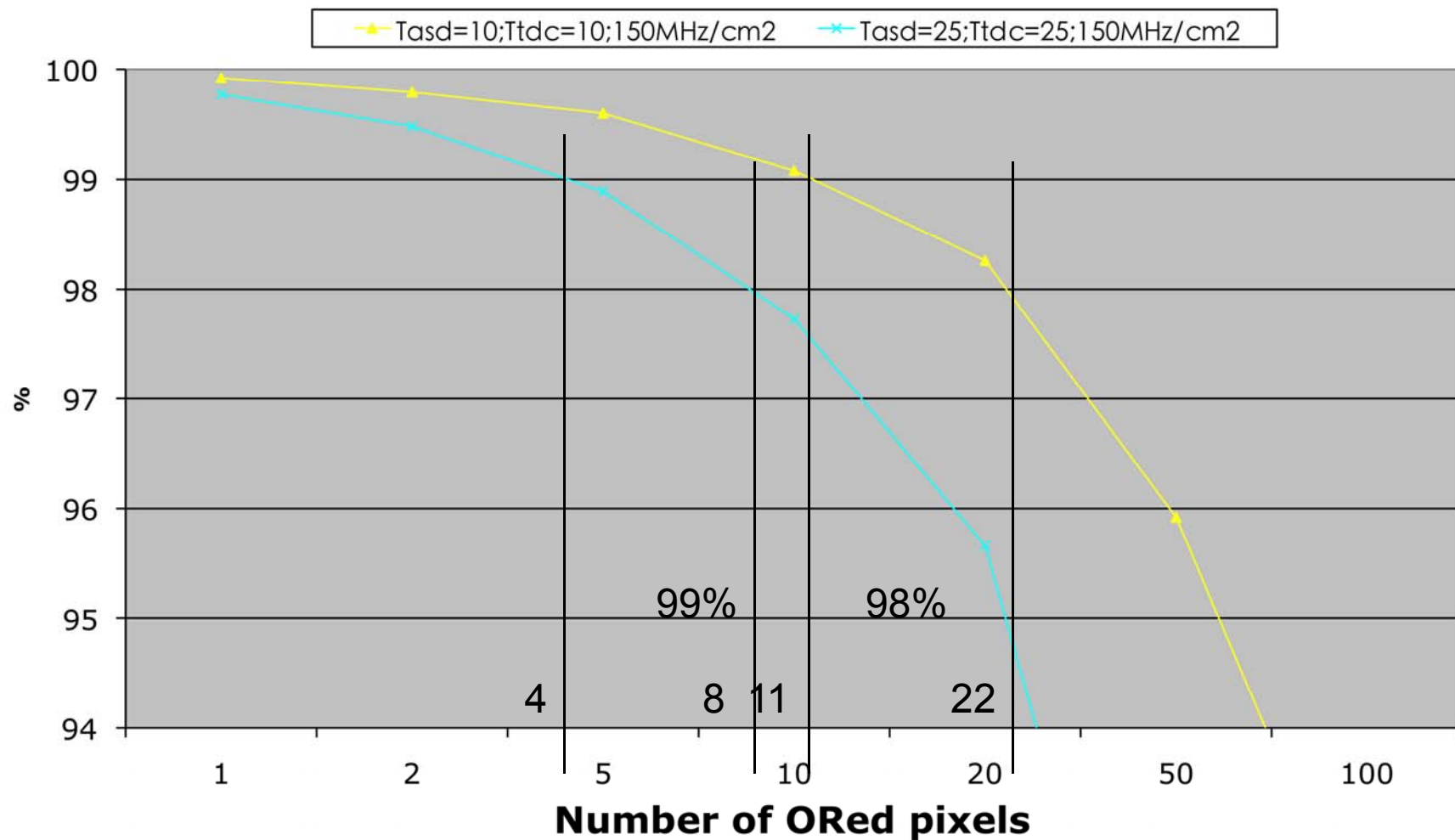


TDC in pixel cell

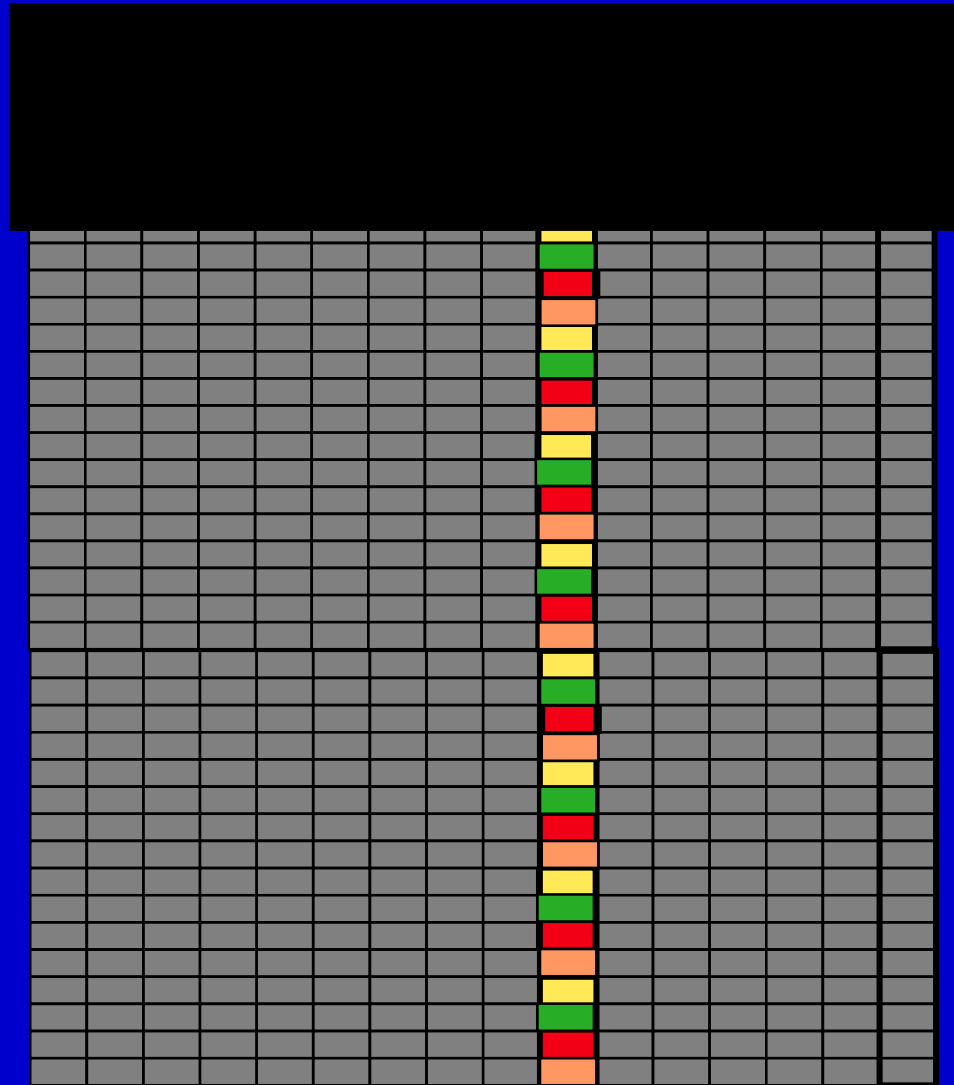
- **Low jitter reference clock routed to each pixel cell on entire chip.**
- **Activity in pixel cell.**
- **Radiation**

Pixel segmentation

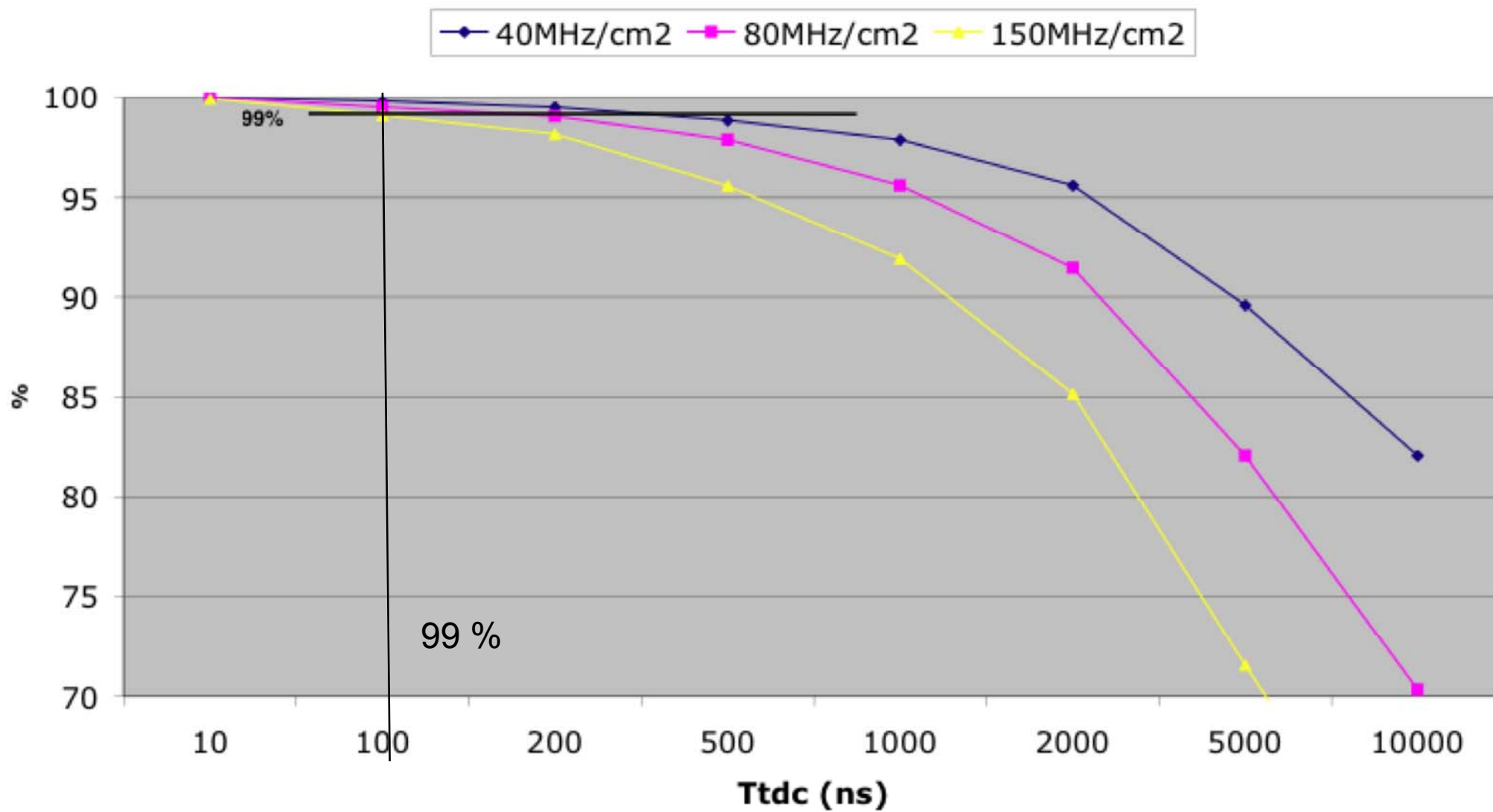
Efficiency 150 MHz/cm² (corresponds to center pixel)
if pixels shared come from different parts in the column the rate decreases



Rate sharing along a column



Efficiency for 1 TDC per pixel ($T_{asd}=10\text{ns}$, $N_{or}=1$)



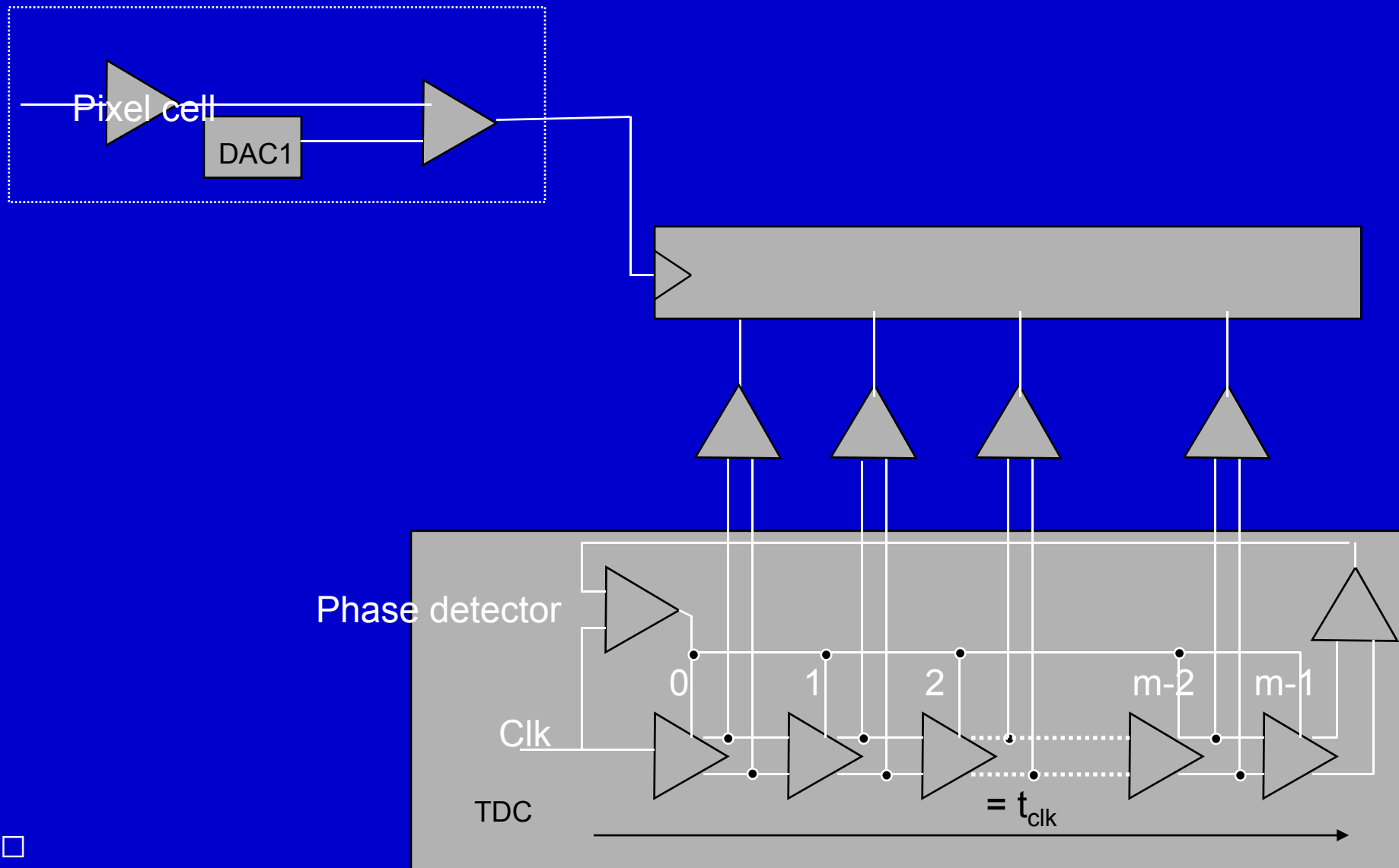
Question

- **How can we find a solution which allows to:**
- **provide timing resolution, sufficient low noise and high data rate**

Design options

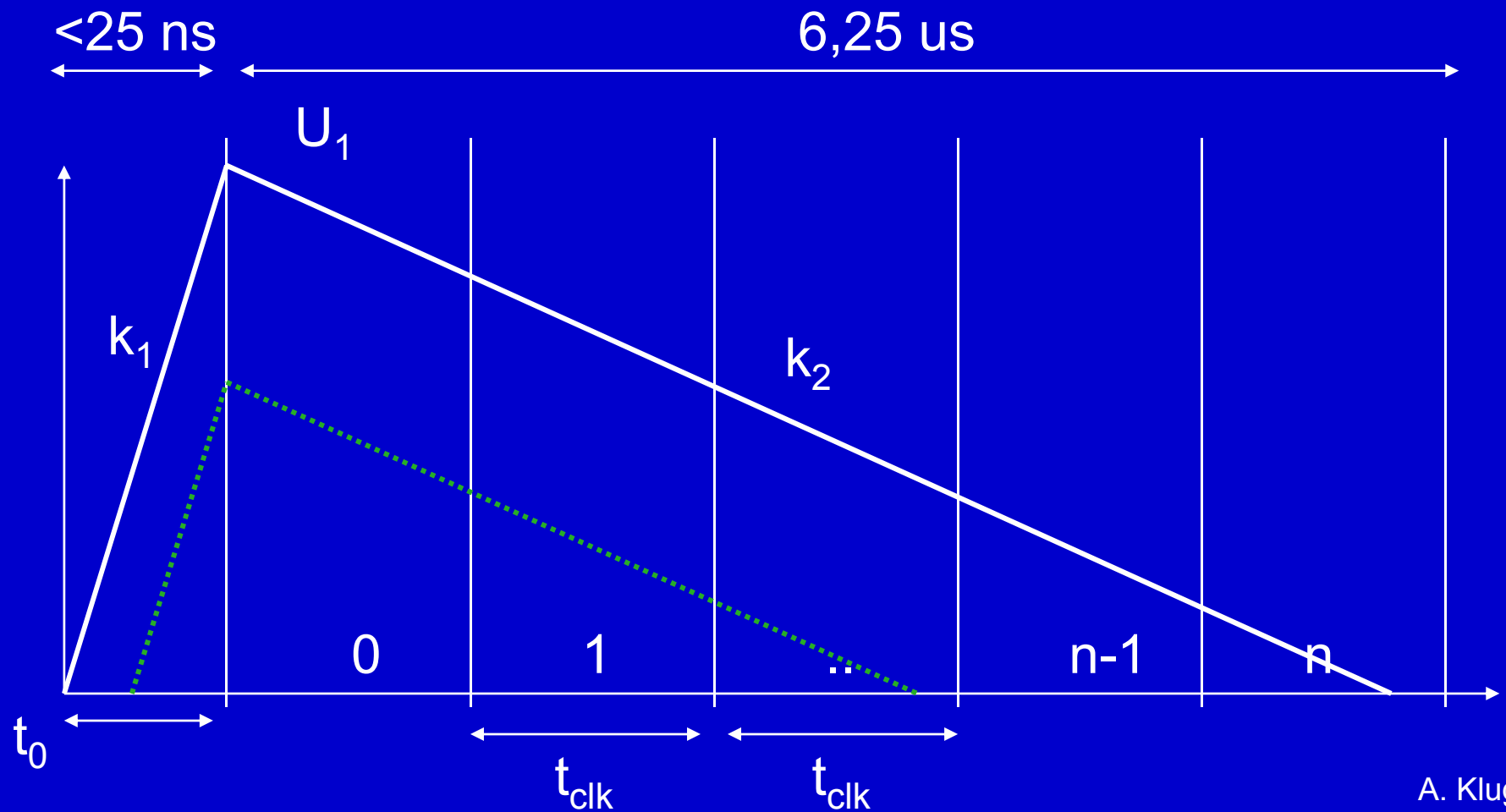
- **Amplifier, Discriminator, time walk compensation:**
 - CFD,
 - TOT
- **TDC**
 - Wilkinson (TDC per pixel)
 - DLL (TDC in end of column)

HPTDC principle



TDC (Wilkinson-dual slope)

$$T_0 = n T_{\text{clk}} k_2 / k_1$$



Demonstrator

- **needs to answer at least following questions:**
 - Can we provide a time resolution of 100 ps rms?
 - Is this also true when we read-out the data?
 - Is front-end robust enough?
 - Is noise separation between analog and digital good enough?
- **What do we need to measure and how?**

Conclusion

- **Specifications**
- **Design options and why?**